

/ Descriptions

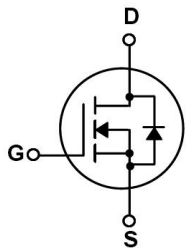
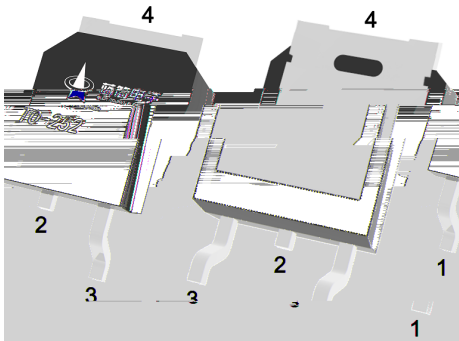
TO-252 SiC N MOS

SiC N-CHANNEL MOSFET in a TO-252 Plastic Package.

/ Features $V_{DS}=800V$ $I_D=7A$ $R_{DS(on)}@15V \leq 650m\Omega$ (Type. 500m Ω) $R_{DS(on)}@18V \leq 600m\Omega$ (Type. 378m Ω)**/ Applications**

LED PD PC

LED driver, PD charger, PC adapter, Air-conditioning, E-bike charger.

/ Equivalent Circuit**/ Pinning**

PIN1 G

PIN 2 D

PIN 3 S

PIN 4 D

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Tc=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	800	V
Continuous DC Drain Current for $R_{th(j-c,typ.)}$, Limited by $T_{VJ(max)}$	$I_D(Tc=25)$	7	A
	$I_D(Tc=100)$	5.7	A
Peak Drain Current, tp Limited by $T_{VJ(max)}$	I_{DM}	12	A
Gate-Source Max Voltage	$V_{GS,max}$	-10/+22	V
Gate-Source Operate Voltage	$V_{GS,op}$	0/+15	V
Single Pulse Avalanche Energy	E_{AS}	10.2	mJ
Power Dissipation or $R_{th(j-c,typ.)}$	$P_D(Tc=25)$	39	W
Operating and Storage Temperature Range	T_{VJ}, T_{STG}	-55 to 175	
MOSFET/Body Diode Junction-Case Thermal Resistance	$R_{th(j-c)}$	3.85	/W

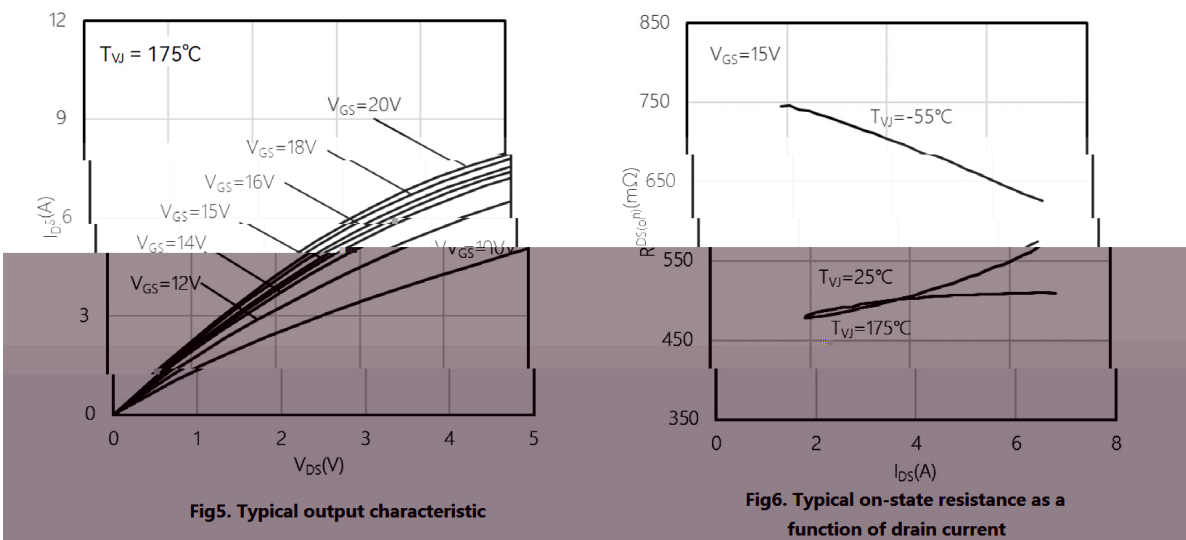
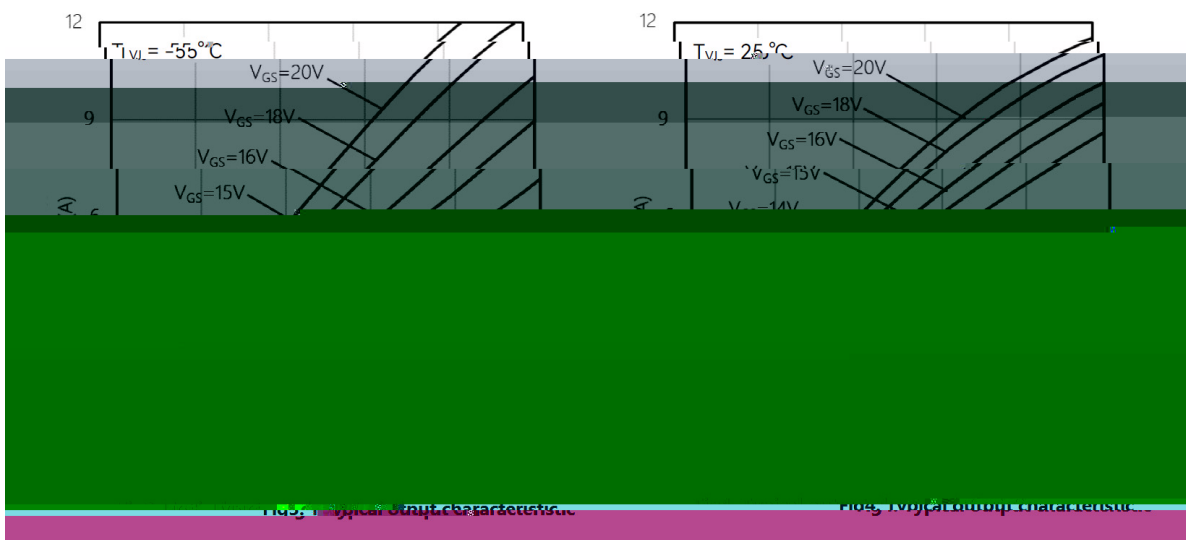
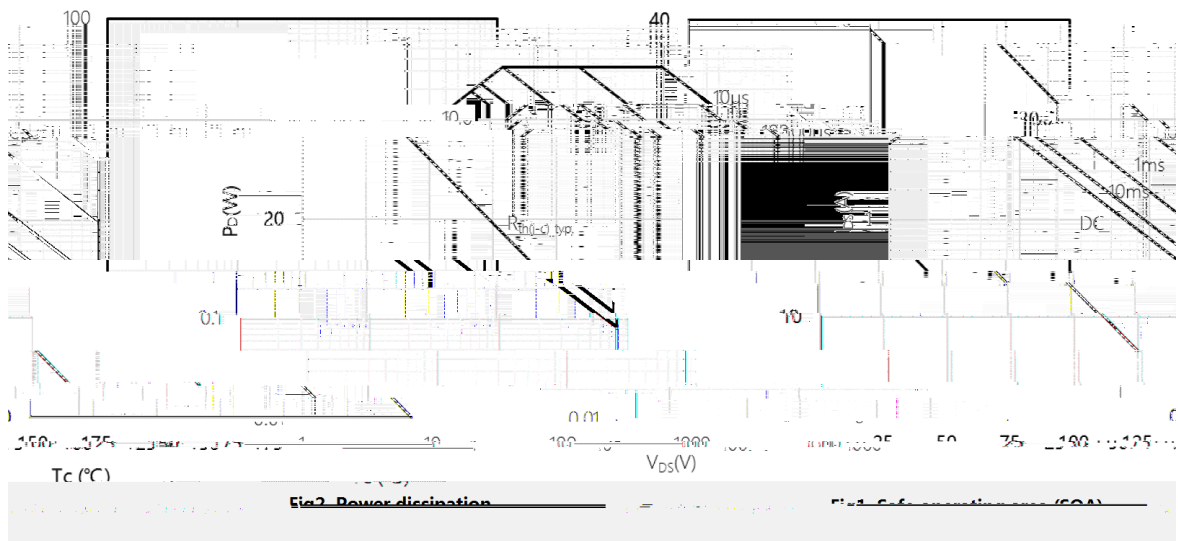
/ Electrical Characteristics(Tc=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=1mA$	800			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=3.5mA$	3		5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=800V$ $V_{GS}=0V$		0.1	20	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=22V$ $V_{DS}=0V$			250	nA
Source-Gate Leakage Current	I_{SGS}	$V_{GS}=-10V$ $V_{DS}=0V$			250	nA
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=15V$ $I_D=4A$		500	650	m Ω
		$V_{GS}=15V$ $I_D=4A$ $T_{VJ}=175$		509		
		$V_{GS}=18V$ $I_D=4A$		378	600	
		$V_{GS}=18V$ $I_D=4A$ $T_{VJ}=175$		454		
Body Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=2A$		3.8		V
Continuous DC Source Current	I_S			6		A
Peak Reverse Drain Current	I_{SM}			12		A
Reverse Recovery Time	t_{rr}	$V_{GS}=0V$, $I_{SD}=4A$, $V_R=400V$, $di/dt=1.1kA/us$		7.9		ns
Reverse Recovery Charge	Q_{rr}			20		nC
Peak Reverse Recovery Current	I_{rrm}			4.2		A
Reverse Recovery Energy	E_{rr}			0.19		μJ

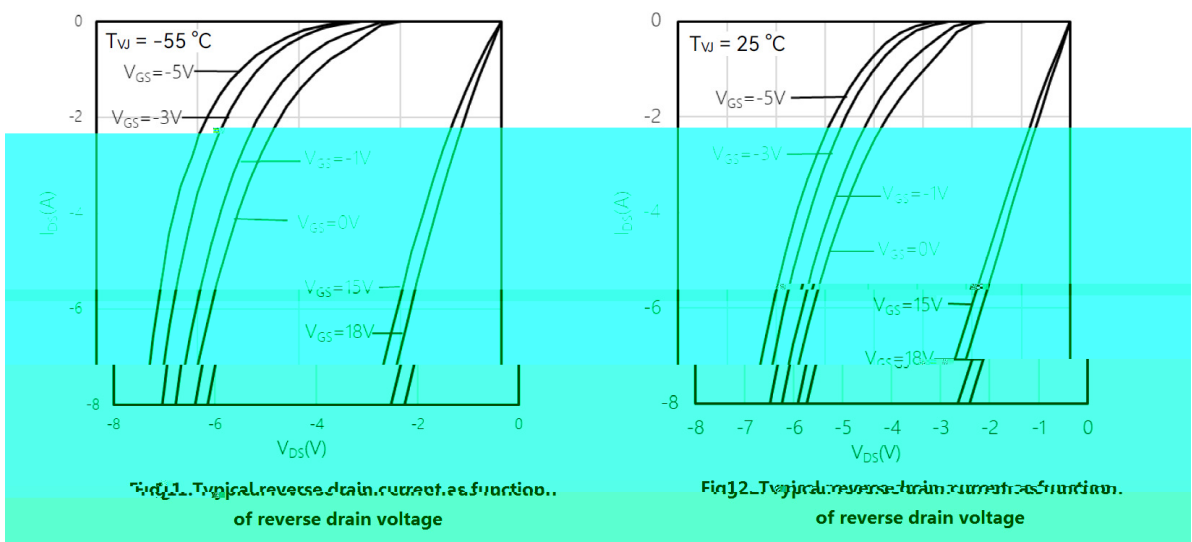
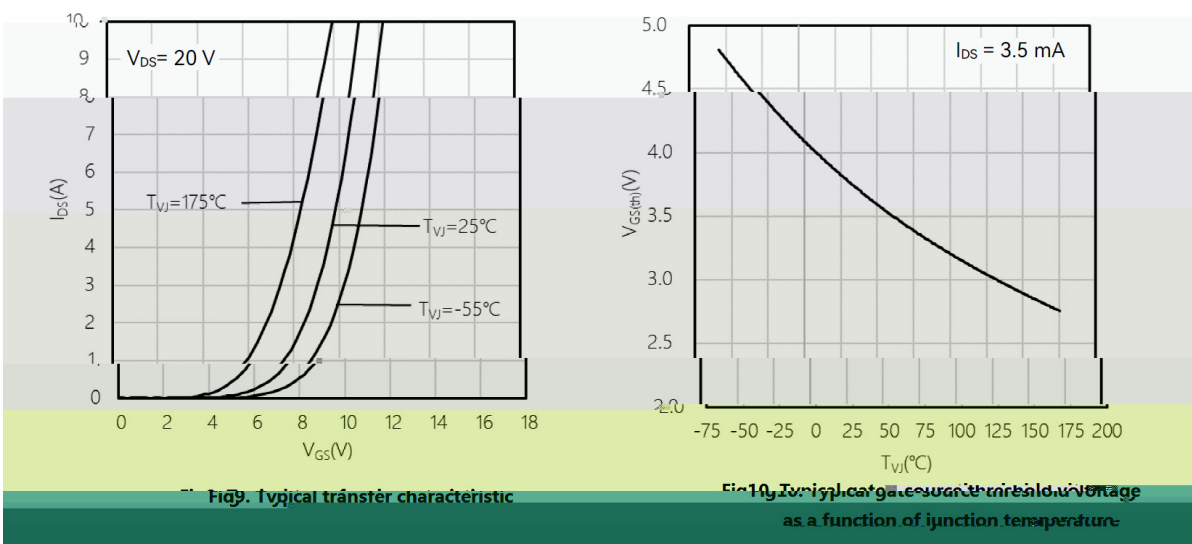
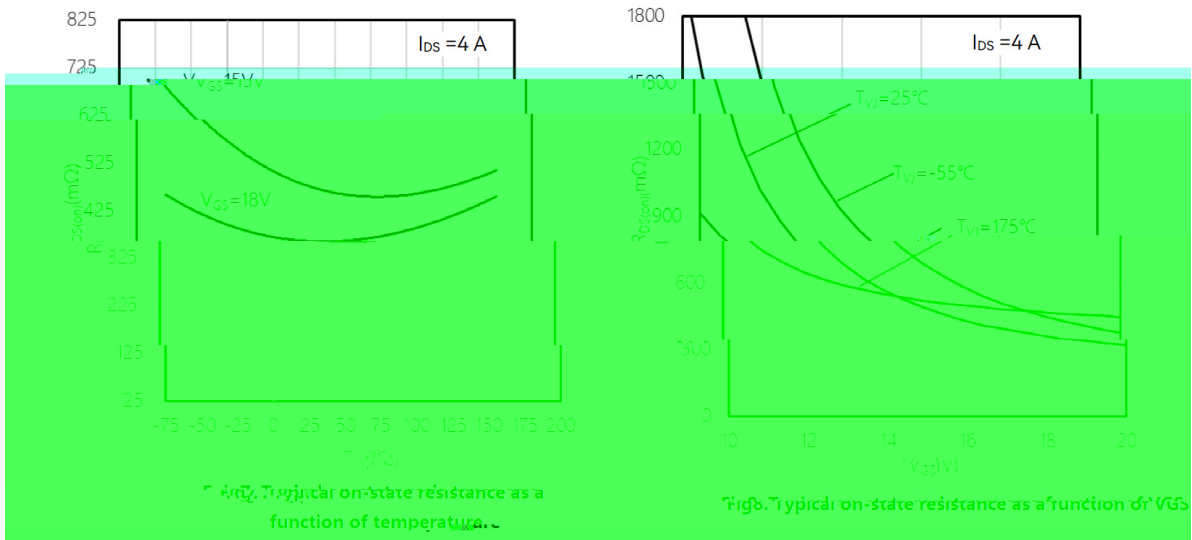
/ Electrical Characteristics(Tc=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=0/15V$ $L=600\mu H$ $V_{DD}=400V$ $I_D=4A$ $R_g=10\Omega$		16.1		ns
Turn-On Rise Time	t_r			13.9		
Turn-Off Delay Time	$t_{d(off)}$			13.3		
Turn-Off Fall Time	t_f			13.7		
Turn-On Switching Loss	E_{on}			41.2		μJ
Turn-Off Switching Loss	E_{off}			3.1		
Total Switching Energy	E_{tot}			44.3		
Gate resistance	R_g	$V_{AC}=25mV$ $f=1MHz$		35		Ω
Input Capacitance	C_{iss}	$V_{DS}=400V$ $V_{GS}=0V$ $f=1MHz$		149		pF
Output Capacitance	C_{oss}			11		
Reverse Transfer Capacitance	C_{rss}			0.8		
Total Gate Charge	Q_g	$V_{GS}=0/15V,$ $V_{DS}=400V,$ $I_D=4A$		6.7		nC
Gate Source Charge	Q_{gs}			3.0		
Gate Drain Charge	Q_{gd}			1.1		

/ Electrical Characteristic Curve



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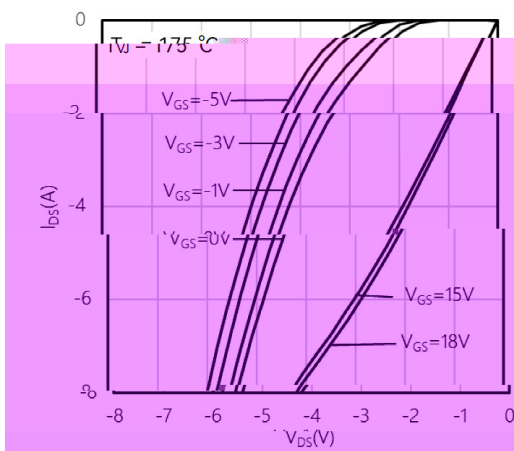


Fig13. Typical reverse drain current as function

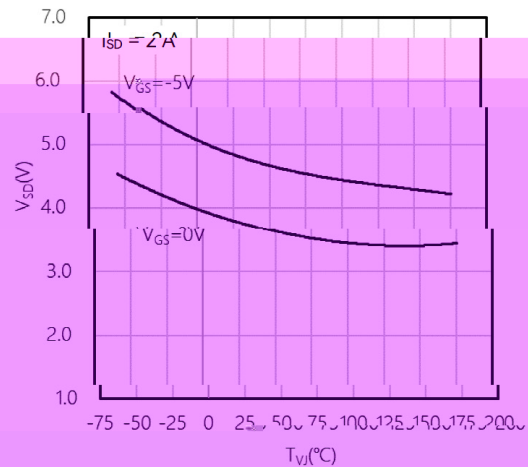


Fig14. Typical reverse drain voltage as a function of junction temperature

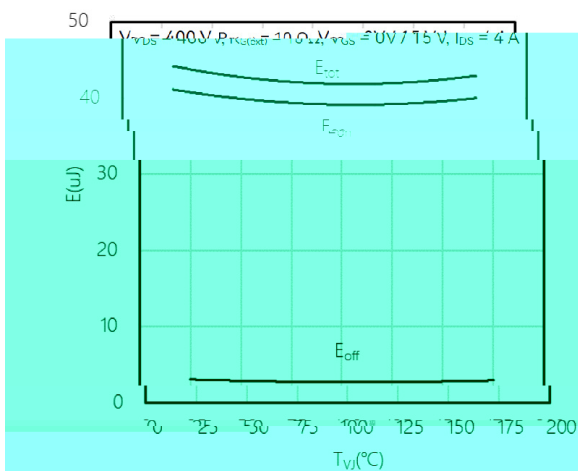


Fig15. Typical switching energy losses as a function of junction temperature, 2nd device own body diode: VGS = 0V

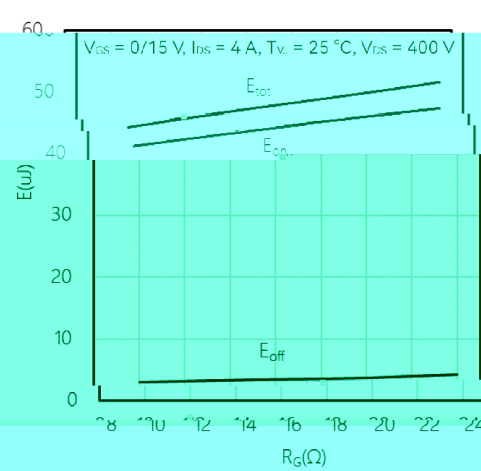


Fig16. Typical switching energy losses as a function of gate resistance, 2nd device own body diode: VGS = 0V

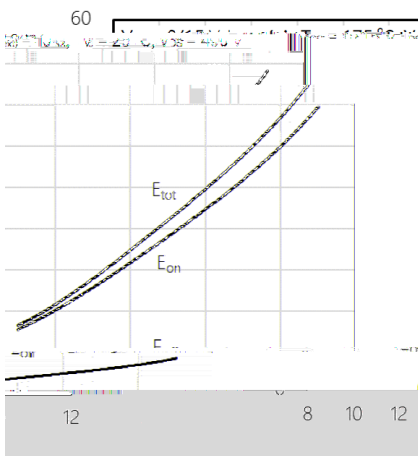


Fig17. Typical switching energy losses as a function of gate resistance, 2nd device own body diode: VGS = 0V

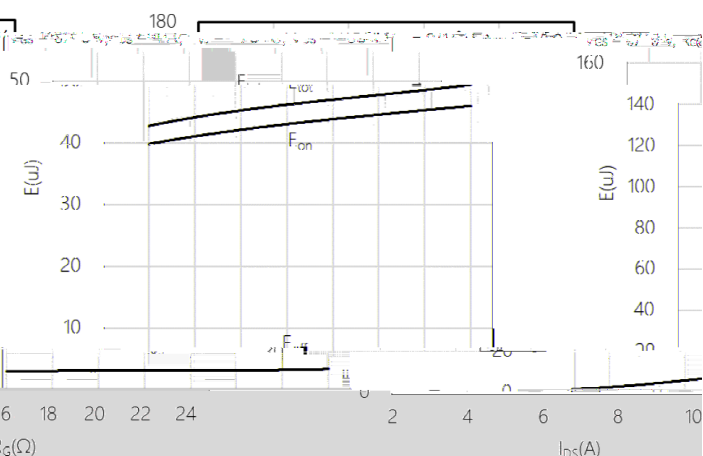
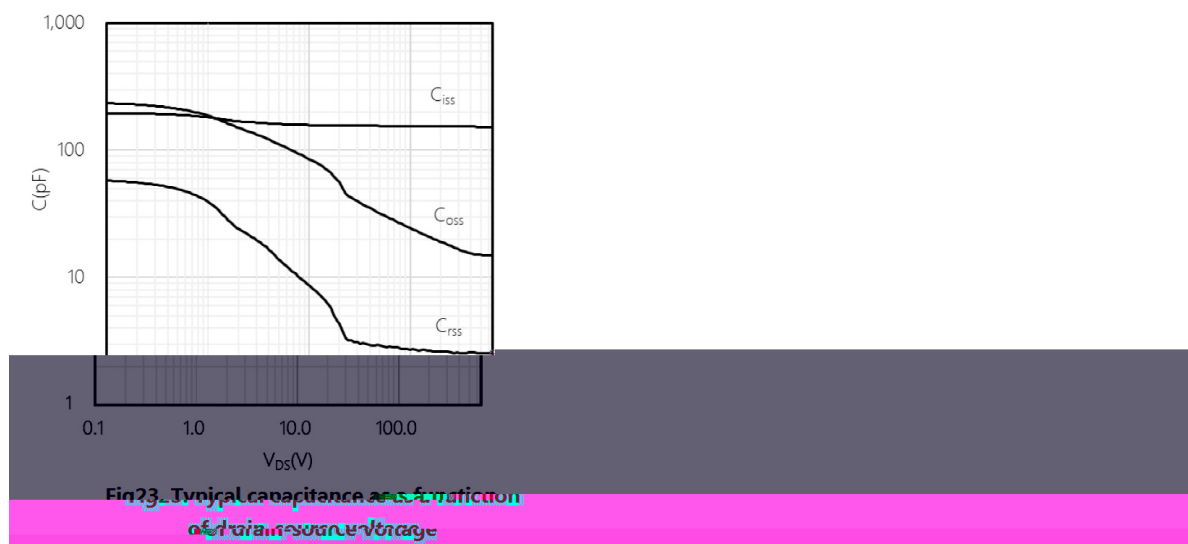
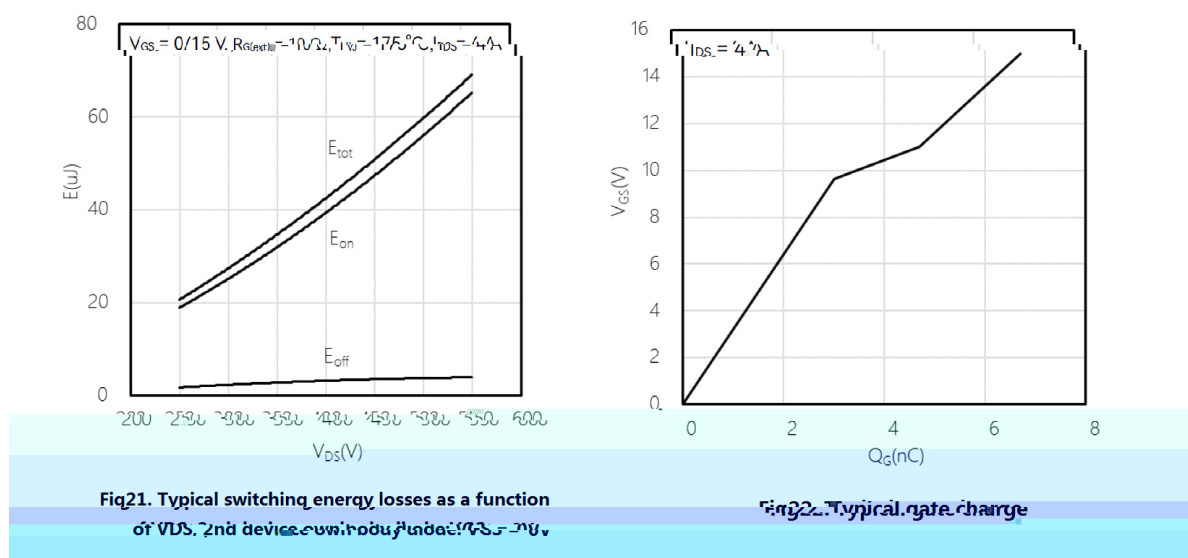
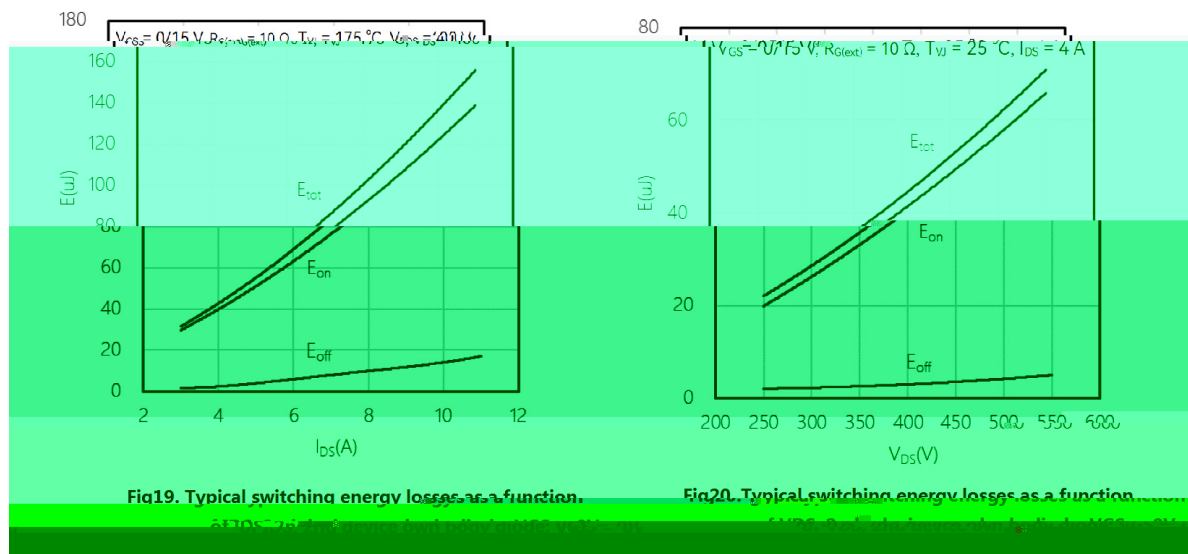


Fig18. Typical switching energy losses as a function of Ids, 2nd device own body diode: VGS = 0V

/ Electrical Characteristic Curve



/ Electrical Characteristic Curve

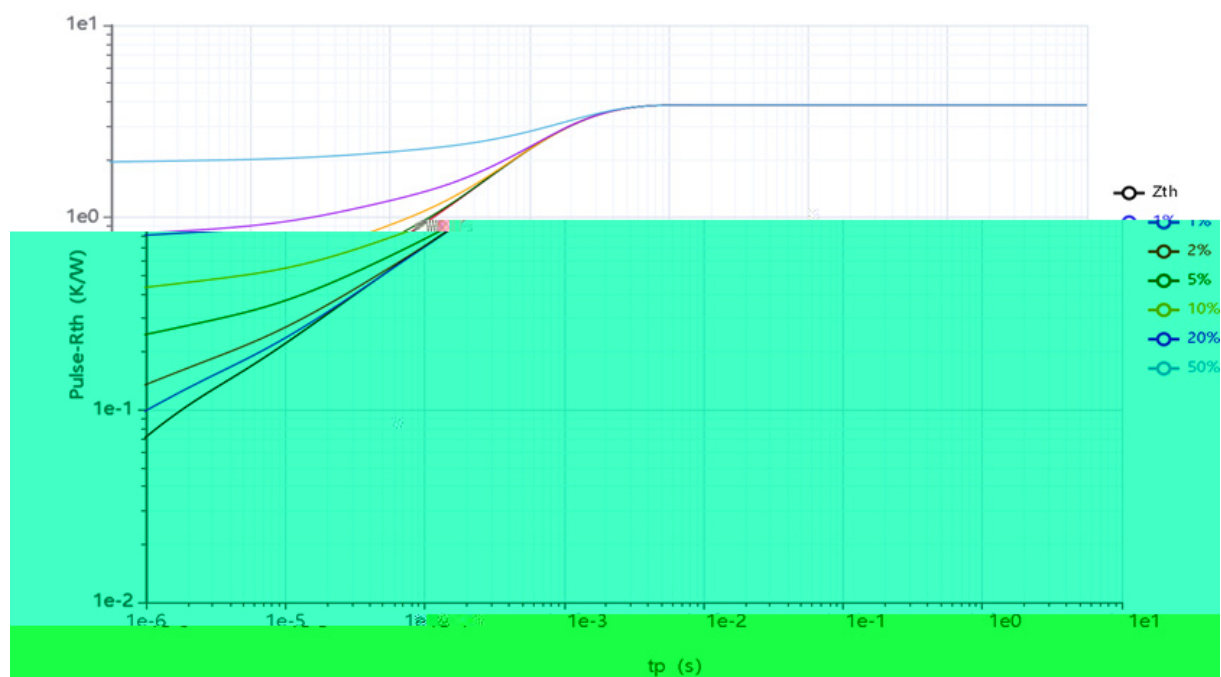
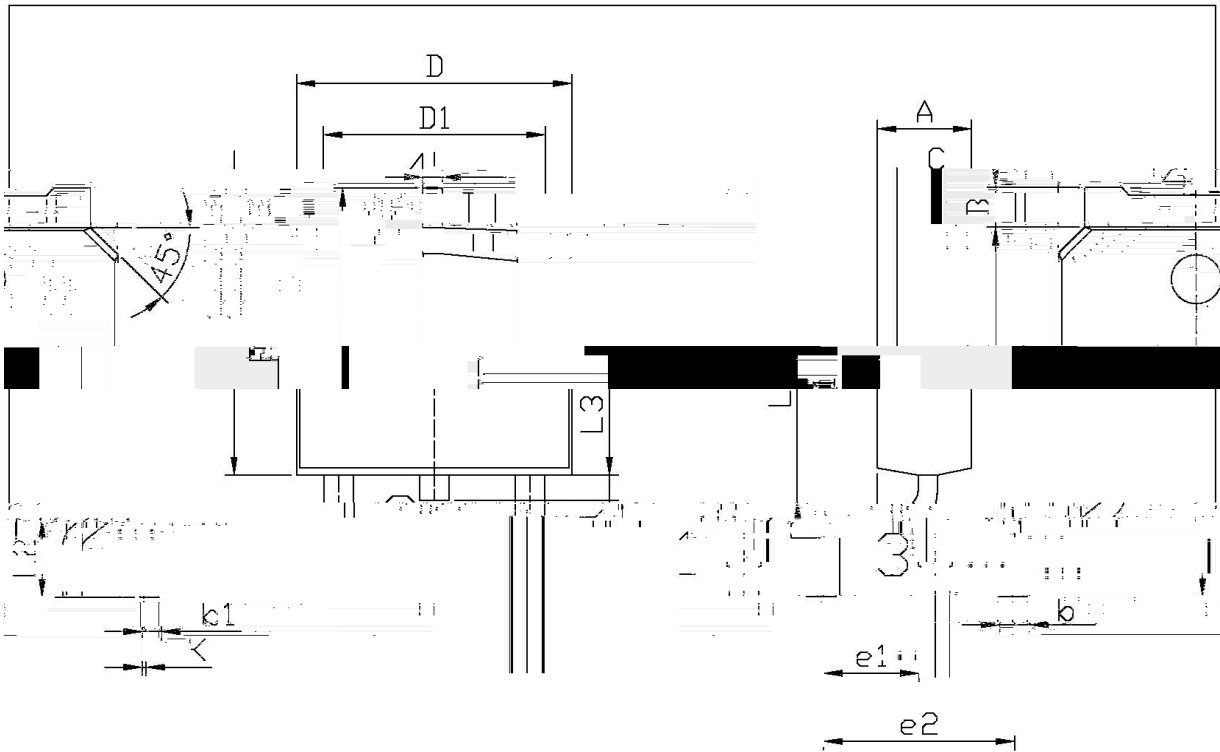


Fig24. Transient thermal resistance (MOSFET)

/ Package Dimensions

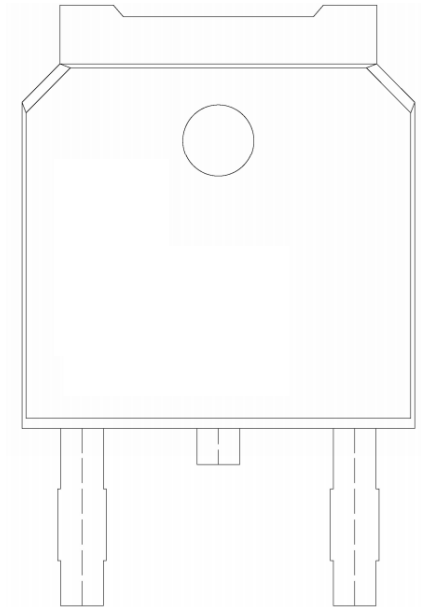


单位: mm

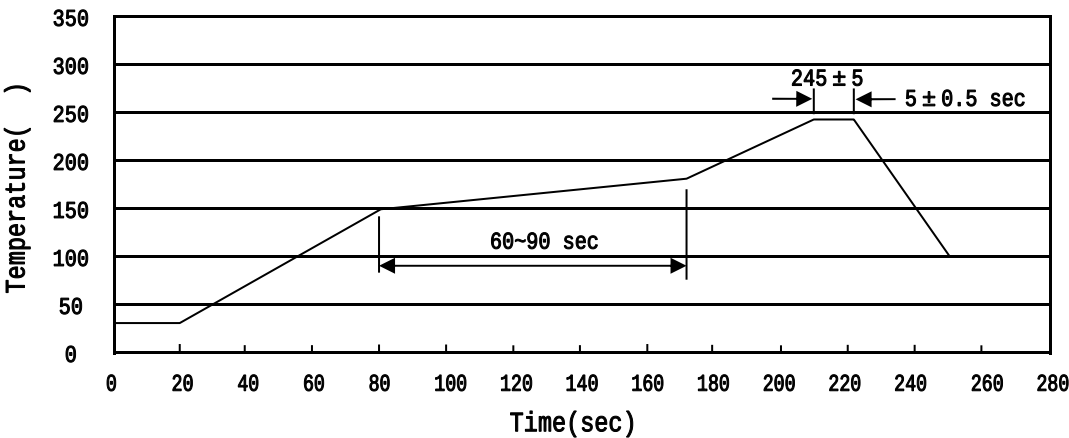
Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	6.25		A ₁	2.20	2.40
B	2.34		B	0.95	1.25
C	4.73		C	0.30	0.50
D	10.35		b1	0.45	0.55
L3	0.60	0.45	L2	0.70	2.00
k1	0.60	0.45	K	0.00	0.10
K	5.10	5.50	D1		6.45

T0-252

/ Marking Instructions



() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|----|-----------|--|
| 1 | 150 | 180 | 60 | 90sec; | 1.Preheating:150~180 °C , Time:60~90sec. |
| 2 | 245±5 | | | 5±0.5sec; | 2.Peak Temp.:245±5 °C , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 °C/sec. |

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm ³)		
TO-252	2,500	2	5,000	6	30,000	13 ×16	360×360×50	380×335×366

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

/ Notices

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